#### 1.0 ELECTRICAL CHARACTERISTICS

#### **Absolute Maximum Ratings†**

| Drain-to-Source Voltage                       | BV <sub>DSS</sub> |
|---|-------------------|
| Drain-to-Gate Voltage                         |                   |
| Gate-to-Source Voltage                        |                   |
| Operating Ambient Temperature, T <sub>A</sub> |                   |
| Storage Temperature, T <sub>S</sub>           |                   |

**† Notice:** Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

#### DC ELECTRICAL CHARACTERISTICS

**Electrical Specifications:**  $T_A = 25^{\circ}$ C unless otherwise specified. All DC parameters are 100% tested at 25°C unless otherwise stated. Pulse test: 300 µs pulse, 2% duty cycle.

| Parameter                                      | Sym.                 | Min.       | Тур. | Max. | Unit  | Conditions   |
|--|----------------------|------------|------|------|-------|--|
| Drain-to-Source Breakdown Voltage              | BV <sub>DSS</sub>    | -200       | _    | _    | V     | $V_{GS} = 0V$ , $I_D = -2$ mA  |
| Gate Threshold Voltage                         | V <sub>GS(th)</sub>  | <b>–</b> 1 | _    | -2.4 | V     | $V_{GS} = V_{DS}$ , $I_D = -1$ mA  |
| Change in V <sub>GS(th)</sub> with Temperature | $\Delta V_{GS(th)}$  | _          | _    | 4.5  | mV/°C | $V_{GS} = V_{DS}$ , $I_D = -1$ mA (Note 1)                                 |
| Gate Body Leakage Current                      | I <sub>GSS</sub>     | _          | _    | -100 | nA    | $V_{GS}$ = ±20V, $V_{DS}$ = 0V   |
|  |                      | _          |      | -10  | μΑ    | V <sub>GS</sub> = 0V,<br>V <sub>DS</sub> = Maximum rating                  |
| Zero-Gate Voltage Drain Current                | I <sub>DSS</sub>     |            |      | -1   | mA    | $V_{DS}$ = 0.8 Maximum rating,<br>$V_{GS}$ = 0V, $T_A$ = 125°C<br>(Note 1) |
| On-State Drain Current                         | 1                    | -0.25      | -0.7 | _    | Α     | $V_{GS} = -4.5V, V_{DS} = -25V$  |
| On-State Drain Current                         | I <sub>D(ON)</sub>   | -0.75      | -2.1 | _    | Α     | $V_{GS} = -10V, V_{DS} = -25V$   |
| Static Drain-to-Source On-State Resistance     | В                    | _          | 10   | 15   | Ω     | $V_{GS} = -4.5V$ , $I_D = -100 \text{ mA}$                                 |
| Static Diani-to-Source Oil-State Resistance    | R <sub>DS(ON)</sub>  | _          | 8    | 12   | Ω     | $V_{GS} = -10V$ , $I_D = -200 \text{ mA}$                                  |
| Change in R <sub>DS(ON)</sub> with Temperature | ΔR <sub>DS(ON)</sub> | _          | _    | 1.7  | %/°C  | $V_{GS} = -10V$ , $I_{D} = -200 \text{ mA}$ (Note 1)                       |

**Note 1:** Specification is obtained by characterization and is not 100% tested.

#### **AC ELECTRICAL CHARACTERISTICS**

**Electrical Specifications:** T<sub>A</sub> = 25°C unless otherwise specified. Specification is obtained by characterization and is not 100% tested.

| Parameter                        | Sym.                | Min. | Тур. | Max. | Unit | Conditions   |
|----------------------------------|---------------------|------|------|------|------|--|
| Forward Transconductance         | G <sub>FS</sub>     | 100  | 250  | _    | mmho | $V_{DS} = -25V$ , $I_{D} = -200$ mA                  |
| Input Capacitance                | C <sub>ISS</sub>    | _    | 75   | 125  | pF   | $V_{GS} = 0V$  |
| Common Source Output Capacitance | Coss                | _    | 20   | 85   | pF   | $V_{DS} = -25V,$                                     |
| Reverse Transfer Capacitance     | C <sub>RSS</sub>    | _    | 10   | 35   | pF   | f = 1 MHz  |
| Turn-On Delay Time               | t <sub>d(ON)</sub>  | _    | _    | 10   | ns   |  |
| Rise Time                        | t <sub>r</sub>      | _    | _    | 15   | ns   | $V_{DD} = -25V,$                                     |
| Turn-Off Delay Time              | t <sub>d(OFF)</sub> | _    | _    | 20   | ns   | $I_D = -750 \text{ mA},$<br>$R_{GEN} = 25\Omega$     |
| Fall Time                        | t <sub>f</sub>      | _    | _    | 15   | ns   | GEN  |
| DIODE PARAMETER                  | _                   |      |      |      |      |  |
| Diode Forward Voltage Drop       | $V_{SD}$            |      | _    | -1.8 | V    | $V_{GS} = 0V$ , $I_{SD} = -500$ mA ( <b>Note 1</b> ) |
| Reverse Recovery Time            | t <sub>rr</sub>     | _    | 300  | _    | ns   | $V_{GS} = 0V, I_{SD} = -500 \text{ mA}$              |

Note 1: Unless otherwise stated, all DC parameters are 100% tested at 25°C. Pulse test: 300 μs pulse, 2% duty cycle

#### **TEMPERATURE SPECIFICATIONS**

| Parameter                     | Sym.           | Min. | Тур. | Max. | Unit | Conditions |
|-------------------------------|----------------|------|------|------|------|------------|
| TEMPERATURE RANGE             |                |      |      |      |      |            |
| Operating Ambient Temperature | T <sub>A</sub> | -55  | _    | +150 | °C   |            |
| Storage Temperature           | T <sub>S</sub> | -55  | _    | +150 | °C   |            |
| PACKAGE THERMAL RESISTANCE    |                |      |      |      |      |            |
| 3-lead SOT-89                 | $\theta_{JA}$  | _    | 133  | _    | °C/W |            |

#### THERMAL CHARACTERISTICS

| Package       | I <sub>D</sub> (Note 1)<br>(Continuous)<br>(mA) | I <sub>D</sub><br>(Pulsed)<br>(A) | Power Dissipation<br>at T <sub>A</sub> = 25°C<br>(Note 2)<br>(W) | I <sub>DR</sub> (Note 1)<br>(mA) | I <sub>DRM</sub><br>(A) |
|---------------|---|-----------------------------------|--|----------------------------------|-------------------------|
| 3-lead SOT-89 | -260  | -2                                | 1.6  | -260                             | -2                      |

Note 1:  $I_D$  (continuous) is limited by maximum rated  $T_J$ .

2: Mounted on an FR5 board, 25 mm x 25 mm x 1.57 mm

#### 2.0 TYPICAL PERFORMANCE CURVES

**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g. outside specified power supply range) and therefore outside the warranted range.

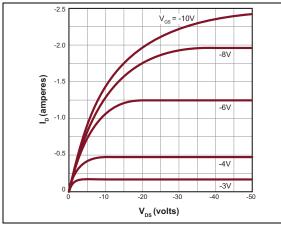


FIGURE 2-1: Output Characteristics.

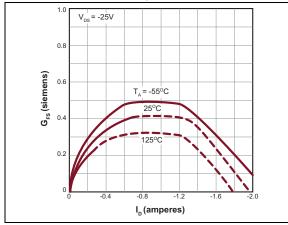
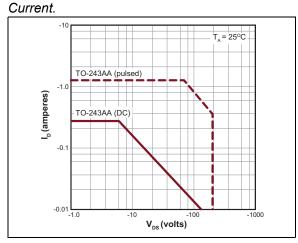


FIGURE 2-2: Transconductance vs. Drain



**FIGURE 2-3:** Maximum Rated Safe Operating Area.

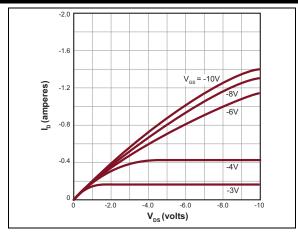
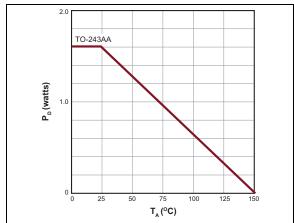
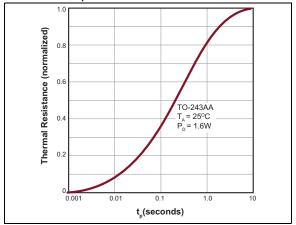


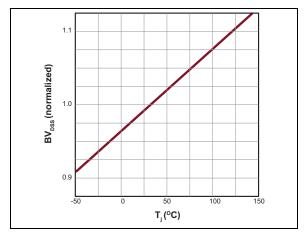
FIGURE 2-4: Saturation Characteristics.



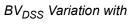
**FIGURE 2-5:** Power Dissipation vs. Ambient Temperature.



**FIGURE 2-6:** Thermal Response Characteristics.



**FIGURE 2-7:**  $BV_D$  Temperature.



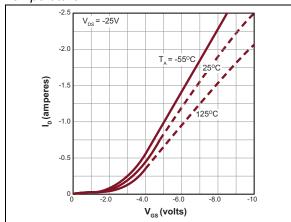
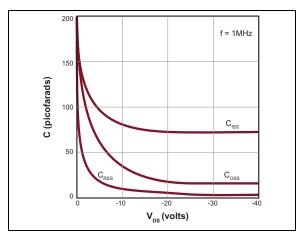
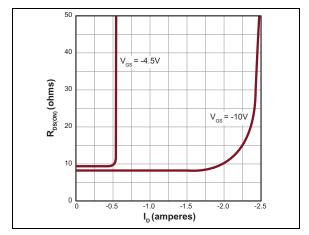


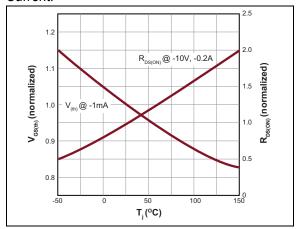
FIGURE 2-8: Transfer Characteristics.



**FIGURE 2-9:** Capacitance vs. Drain-to-Source Voltage.



**FIGURE 2-10:** On-Resistance vs. Drain Current.



**FIGURE 2-11:**  $V_{GS(th)}$  and  $R_{DS}$  Variation with Temperature.

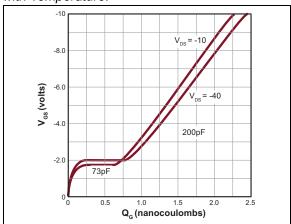


FIGURE 2-12: Gate Drive Dynamic Characteristics.

## **TP2520**

#### 3.0 PIN DESCRIPTION

The details on the pins of TP2520 are listed in Table 3-1. Refer to **Package Type** for the location of pins.

TABLE 3-1: PIN FUNCTION TABLE

| Pin Number | Pin Name | Description |  |  |  |  |  |  |
|------------|----------|-------------|--|--|--|--|--|--|
| 1          | Gate     | Gate        |  |  |  |  |  |  |
| 2,4        | Drain    | Drain       |  |  |  |  |  |  |
| 3          | Source   | Source      |  |  |  |  |  |  |

#### 4.0 FUNCTIONAL DESCRIPTION

Figure 4-1 illustrates the switching waveforms and test circuit for TP2520.

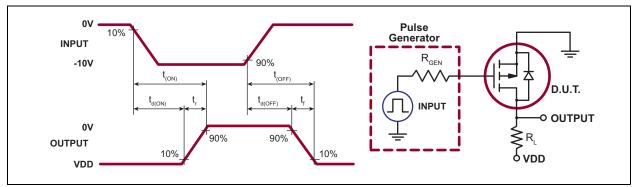


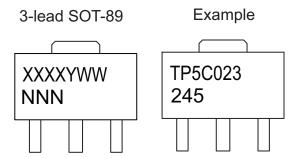
FIGURE 4-1: Switching Waveforms and Test Circuit.

TABLE 4-1: PRODUCT SUMMARY

| BV <sub>DSS</sub> /BV <sub>DGS</sub><br>(V) | R <sub>DS(ON)</sub><br>(Maximum)<br>(Ω) | V <sub>GS(TH)</sub><br>(Maximum)<br>(V) | I <sub>D(ON)</sub><br>(Minimum)<br>(mA) |
|---|---|---|---|
| -200  | 12                                      | -2.4                                    | <del>-</del> 750                        |

#### 5.0 PACKAGING INFORMATION

#### 5.1 Package Marking Information



Legend: XX...X Product Code or Customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

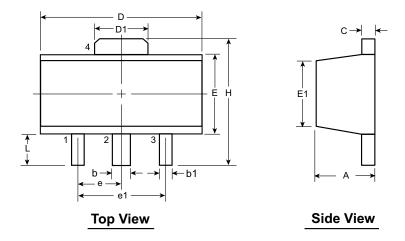
e3 Pb-free JEDEC® designator for Matte Tin (Sn)

This package is Pb-free. The Pb-free JEDEC designator (e3)

can be found on the outer packaging for this package.

**Note**: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for product code or customer-specific information. Package may or not include the corporate logo.

## 3-Lead TO-243AA (SOT-89) Package Outline (N8)



Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

| Symbo           | ol  | Α    | b    | b1   | С    | D    | D1   | E    | E1                | е           | e1          | Н    | L                 |
|-----------------|-----|------|------|------|------|------|------|------|-------------------|-------------|-------------|------|-------------------|
|                 | MIN | 1.40 | 0.44 | 0.36 | 0.35 | 4.40 | 1.62 | 2.29 | 2.00 <sup>†</sup> |             |             | 3.94 | 0.73 <sup>†</sup> |
| Dimensions (mm) | NOM | -    | -    | -    | -    | -    | -    | -    | -                 | 1.50<br>BSC | 3.00<br>BSC | -    | -                 |
| (*****)         | MAX | 1.60 | 0.56 | 0.48 | 0.44 | 4.60 | 1.83 | 2.60 | 2.29              |             |             | 4.25 | 1.20              |

JEDEC Registration TO-243, Variation AA, Issue C, July 1986. † This dimension differs from the JEDEC drawing Drawings not to scale.

# **TP2520**

NOTES:

### APPENDIX A: REVISION HISTORY

### Revision A (June 2020)

- Converted DSFP-TP2520 to Microchip DS20005966A
- Added a pin function table
- Changed the package marking format
- Made minor text changes throughout the document

### PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

| PART NO<br>Device | XX<br>Packa<br>Option |   | - X - X<br>   <br>Environmental Media Type   | Example:  a) TP2520N8-G: | P-Channel Enhancement-<br>Mode, Vertical DMOS FET,<br>3-lead SOT-89, 2000/Reel |
|-------------------|-----------------------|---|--|--------------------------|--|
| Device:           | TP2520                | = | P-Channel Enhancement-Mode Vertical DMOS FET |                          | 0.000 00, 2000.000   |
| Package:          | N8                    | = | 3-lead SOT-89                                |                          |  |
| Environmental:    | G                     | = | Lead (Pb)-free/RoHS-compliant Package        |                          |  |
| Media Type:       | (blank)               | = | 2000/Reel for an N8 Package                  |                          |  |
|                   |                       |   |  |                          |  |
|                   |                       |   |  |                          |  |

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